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# 1 Electrical ratings

Table 1. Absolute maximum ratings

		Value		
Symbol	Parameter	TO-220/D <sup>2</sup> PAK I <sup>2</sup> PAK/TO-247	TO-220FP	Unit
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	500		V
V <sub>DGR</sub>	Drain-gate voltage ( $R_{GS} = 20KΩ$ )	500		V
V <sub>GS</sub>	Gate-source voltage	± 30		٧
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25°C	14	14 <sup>(1)</sup>	А
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> =100°C			А
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	56	56 <sup>(1)</sup>	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25°C	160	40	W
	Derating Factor	1.28	0.32	W/°C
I <sub>GS</sub>	Gate-source current (DC)	± 20		mA
Vesd(G-S)	G-S ESD (HBM C=100pF, R=1.5k $\Omega$ )	4000		KV
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	4.5		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T <sub>C</sub> =25°C)	2500		V
T <sub>J</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-50 to 150°C		°C

<sup>1.</sup> Limited only by maximum temperature allowed

Table 2. Thermal data

		Value					
Symbol	Parameter	TO-220 I <sup>2</sup> PAK	D <sup>2</sup> PAK	TO-220FP	TO-247	Unit	
R <sub>thj-case</sub>	Thermal resistance junction-case Max	0.78		3.1	0.78	°C/W	
Rthj-pcb <sup>(1)</sup>	Thermal resistance junction-pcb max	60				°C/W	

<sup>2.</sup> Pulse width limited by safe operating area

<sup>3.</sup>  $I_{SD} \leq 4A$ , di/dt  $200A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_j \leq T_{JMAX}$ 

#### Table 2. Thermal data

R <sub>thj-a</sub>	Thermal resistance junction-ambient max	62.5	50	°C/W
I i	Maximum lead temperature for soldering purpose	300		°C

<sup>1.</sup> When mounted on minimum foot-print

#### Table 3. Avalanche characteristics

Symbol	Symbol Parameter		Unit
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	14	Α
E <sub>AS</sub>	Single pulse avalanche energy (starting Tj=25°C, Id=I <sub>AR</sub> , V <sub>DD</sub> =50V)	300	mJ

#### Table 4. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
BV <sub>GSO</sub> <sup>(1)</sup>	Gate-source breakdown voltage	Igs=±1mA (Open Drain)	30			٧

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2 Electrical characteristics

(T<sub>CASE</sub>=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	500			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)				1 50	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20V			±10	μΑ
V <sub>GS(th)</sub>	Gate threshold voltage	shold voltage $V_{DS} = V_{GS}$ , $I_D = 100\mu A$		3.75	4.5	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7A		0.30	0.34	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} = 15V$ , $I_D = 7A$		12		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> =25V, f=1 MHz, V <sub>GS</sub> =0		2260 264 64		pF pF pF
C <sub>oss eq</sub> <sup>(2)</sup> .	Equivalent output capacitance	V <sub>GS</sub> =0, V <sub>DS</sub> =0V to 400V		150		pF
$egin{array}{c} Q_{ m g} \ Q_{ m gd} \end{array}$	Total gate charge Gate-source charge Gate-drain charge	V <sub>DD</sub> =400V, I <sub>D</sub> = 14A V <sub>GS</sub> =10V		76 15 40	106	nC nC nC
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD}$ =250 V, $I_{D}$ =7A, $R_{G}$ =4.7 $\Omega$ , $V_{GS}$ =10V (see Figure 18)		20 23 62 15		ns ns ns ns

<sup>1.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

<sup>2.</sup>  $C_{oss\ eq.}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  inceases from 0 to 80%  $V_{DSS}$ 

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I <sub>SD</sub>	Source-drain current			14		Α
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)			56		Α
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	I <sub>SD</sub> =14A, V <sub>GS</sub> =0			1.6	٧
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ =14A, di/dt = 100A/ $\mu$ s, $V_{DD}$ =29V, Tj=150°C		428 4.2 20		ns μC A

<sup>1.</sup> Pulse width limited by safe operating area

<sup>2.</sup> Pulsed: pulse duration=300 $\mu$ s, duty cycle 1.5%

### 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220 D2PAK/I2PAK

Figure 2. Thermal impedance for TO- 220 D2PAK/I2PAK

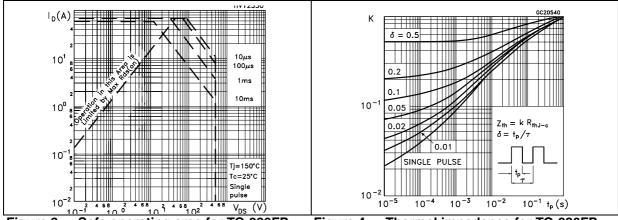


Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

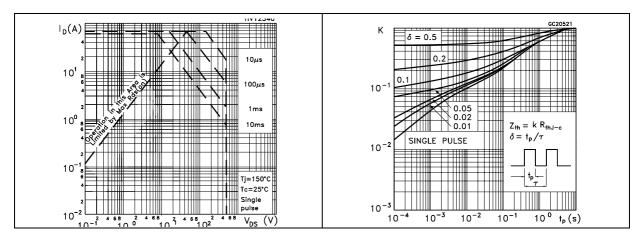


Figure 5. Safe operating area for TO-247

Figure 6. Thermal impedance for TO-247

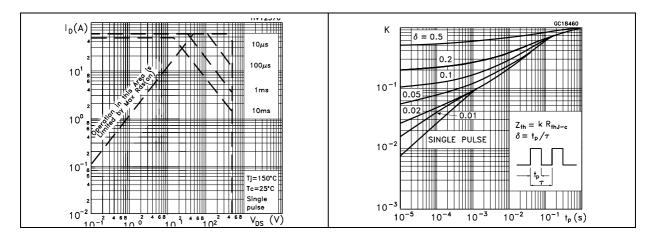
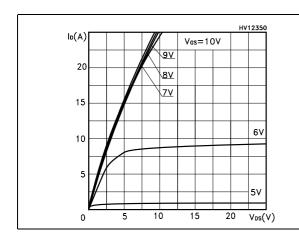


Figure 7. Output characterisics

Figure 8. Transfer characteristics



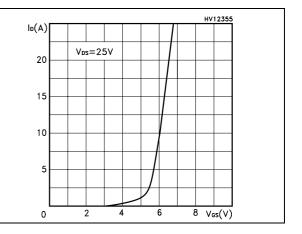
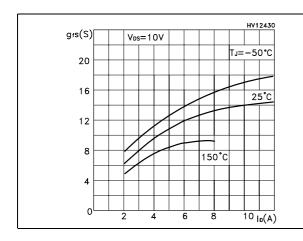


Figure 9. Transconductance

Figure 10. Static drain-source on resistance



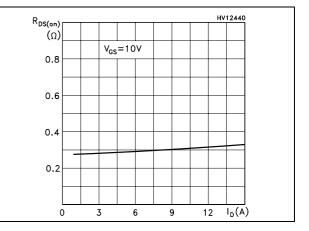
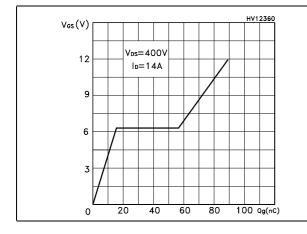


Figure 11. Gate charge vs gate-source voltage Figure 12. Capacitance variations



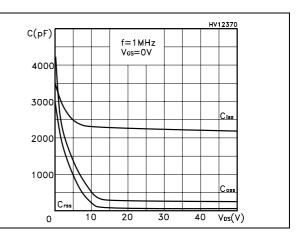
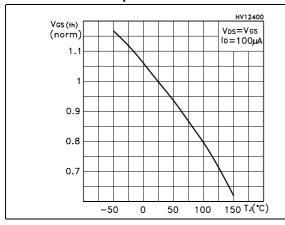


Figure 13. Normalized gate threshold voltage Figure vs temperature

Figure 14. Normalized on resistance vs temperature



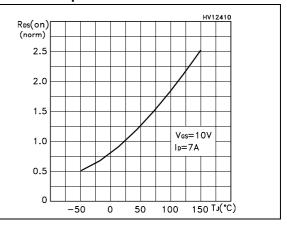
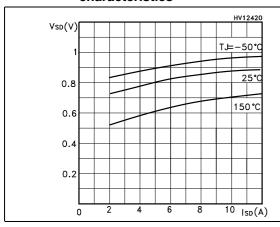


Figure 15. Source-drain diode forward characteristics

Figure 16. Normalized  $\mathbf{B}_{\text{VDSS}}$  vs temperature



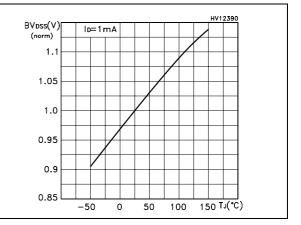
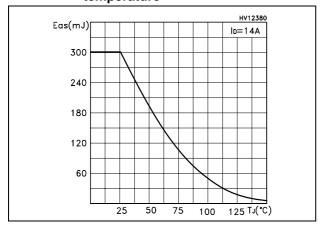


Figure 17. Maximum avalanche energy vs temperature



#### **Test circuit** 3

Figure 18. Switching times test circuit for resistive load

Figure 19. Gate charge test circuit

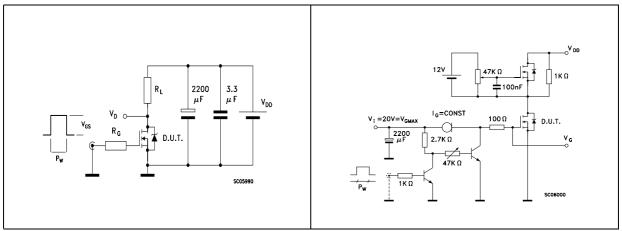


Figure 20. Test circuit for inductive load switching and diode recovery times

Figure 21. Unclamped Inductive load test circuit

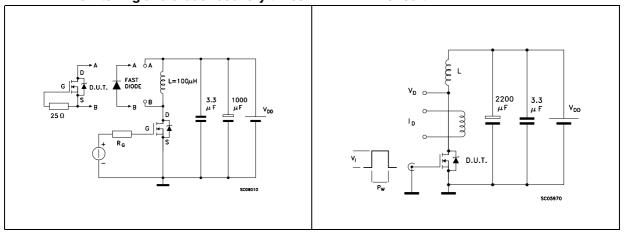
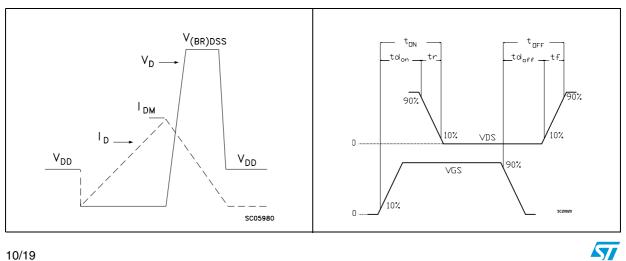


Figure 22. Unclamped inductive waveform

Figure 23. Switching time waveform

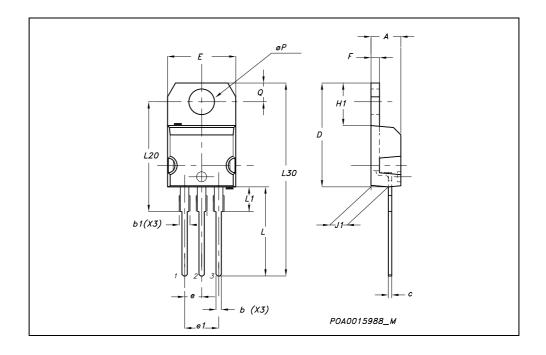


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

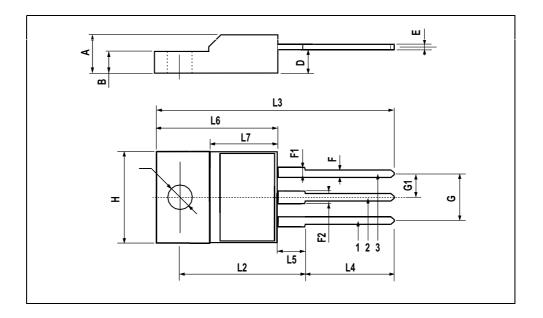
### **TO-220 MECHANICAL DATA**

DIM.		mm.	inch			
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



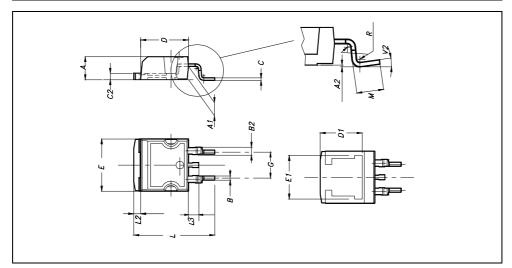
#### **TO-220FP MECHANICAL DATA**

DIM.		mm.			inch	
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



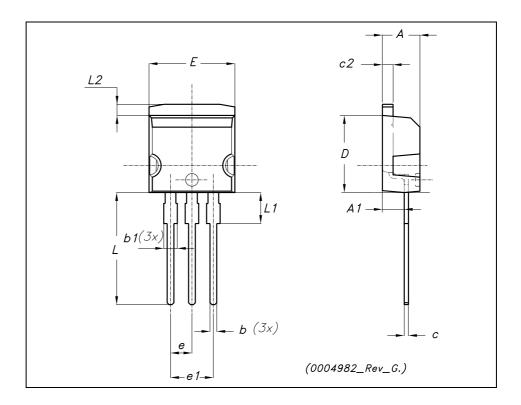
### D<sup>2</sup>PAK MECHANICAL DATA

DIM.		mm.			inch	
DIW.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	O <sub>ō</sub>		4º			



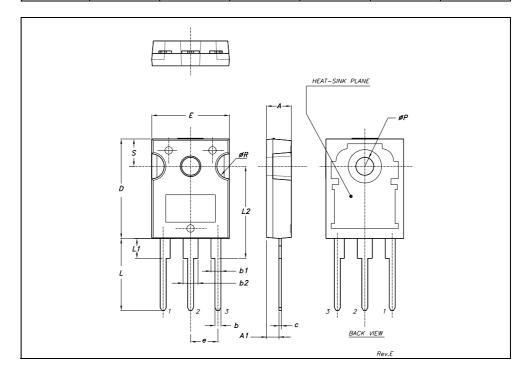
## TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



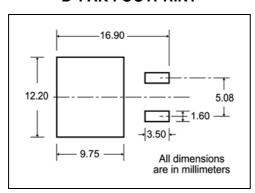
### **TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
С	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
е		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øΡ	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

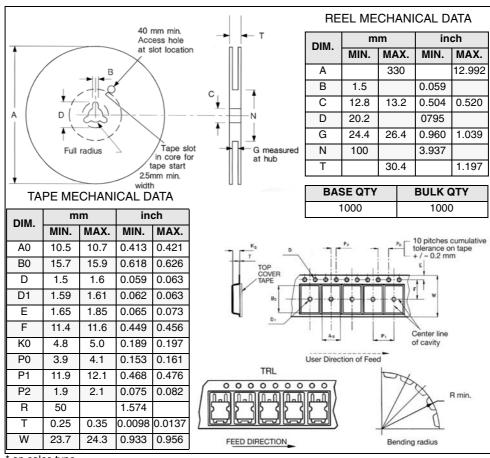


## 5 Packaging mechanical data

### D<sup>2</sup>PAK FOOTPRINT



#### **TAPE AND REEL SHIPMENT**



<sup>\*</sup> on sales type

# 6 Revision history

Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	2	Complete version
20-Jul-2006	3	New template, no content change
05-Jan-2007	4	Modified unit on <i>On/off states</i>

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